IntelliEPI has successfully developed carbon doping capability using CBr4 gas source

- Reproducible InGaAs carbon doping up to 1E20 cm-3
- Excellent InGaAs material quality (mobility and x-ray FWHM)
- No memory effects
- Across 4in wafer uniformity (<0.5%)
- GaAs carbon doping up to 1E20 cm-3
Magnetoresistance measurement using Lehighton shows the resistivity across 4” wafer grown from a 4x4 MBE system. The film thickness and the hole mobility is 350 nm and 60 cm$^2$/Vs, respectively.